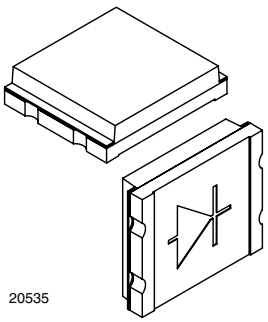
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TEMD5010X01

Vishay Semiconductors

Silicon PIN Photodiode



FEATURES

- Package type: surface mount
- Package form: top view
- Dimensions (L x W x H in mm): 5 x 4.24 x 1.12
- Radiant sensitive area (in mm^2): 7.5
- AEC-Q101 qualified
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 65°$
- Floor life: 72 h, MSL 4, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Find out more about Vishay's Automotive Grade Product requirements at: www.vishay.com/applications

Pb-free

e4

RoHS COMPLIANT

AUTOMOTIVE GRADE

DESCRIPTION

TEMD5010X01 is a high speed and high sensitive PIN photodiode. It is a miniature surface mount device (SMD) including the chip with a 7.5 mm^2 sensitive area detecting visible and near infrared radiation.

APPLICATIONS

- High speed photo detector

PRODUCT SUMMARY

COMPONENT	I_{ra} (µA)	φ (deg)	$\lambda_{0.1}$ (nm)
TEMD5010X01	55	± 65	430 to 1100

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TEMD5010X01	Tape and reel	MOQ: 1500 pcs, 1500 pcs/reel	Top view

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	60	V
Power dissipation	$T_{amb} \leq 25$ °C	P_V	215	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 40 to + 110	°C
Soldering temperature	Acc. reflow solder profile fig. 8	T_{sd}	260	°C
Thermal resistance junction/ambient		R_{thJA}	350	K/W

Note

T_{amb} = 25 °C, unless otherwise specified

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TEMD5010X01

Vishay Semiconductors — Silicon PIN Photodiode

BASIC CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I_F = 50 mA	V_F		1	1.3	V
Breakdown voltage	I_R = 100 µA, E = 0	$V_{(BR)}$	60			V
Reverse dark current	V_R = 10 V, E = 0	I_{ro}		2	30	nA
Diode capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_D		70		pF
	V_R = 3 V, f = 1 MHz, E = 0	C_D		25	40	pF
Open circuit voltage	E_e = 1 mW/cm², λ = 950 nm	V_o		350		mV
Temperature coefficient of V_o	E_e = 1 mW/cm², λ = 950 nm	TK_{Vo}		- 2.6		mV/K
Short circuit current	E_e = 1 mW/cm², λ = 950 nm	I_k		50		µA
Temperature coefficient of I_k	E_e = 1 mW/cm², λ = 950 nm	TK_{Ik}		0.1		%/K
Reverse light current	E_e = 1 mW/cm², λ = 950 nm, V_R = 5 V	I_{ra}	45	55		µA
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λ_p		940		nm
Range of spectral bandwidth		$\lambda_{0.1}$		430 to 1100		nm
Noise equivalent power	V_R = 10 V, λ = 950 nm	NEP		4×10^{-14}		W/√Hz
Rise time	V_R = 10 V, R_L = 1 kΩ, λ = 820 nm	t_r		100		ns
Fall time	V_R = 10 V, R_L = 1 kΩ, λ = 820 nm	t_f		100		ns

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

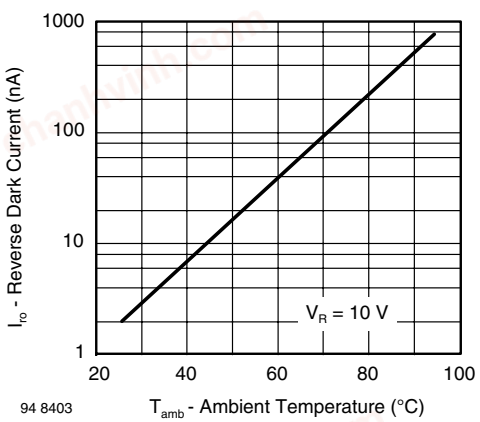


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

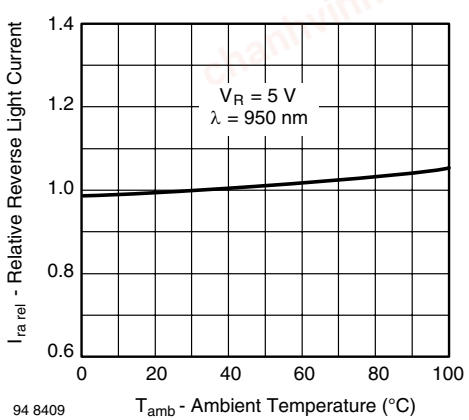


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

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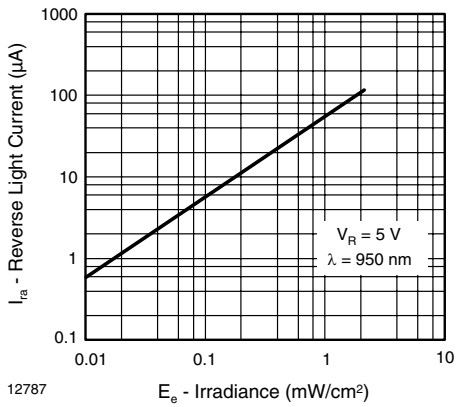


Fig. 3 - Reverse Light Current vs. Irradiance

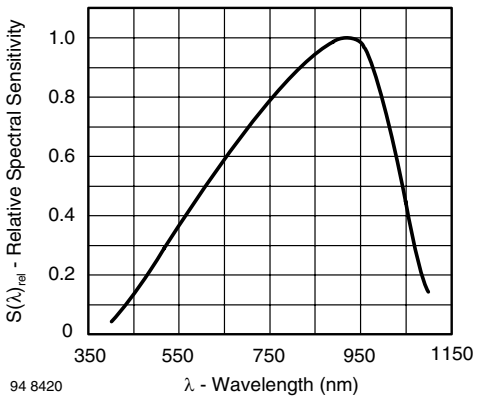


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

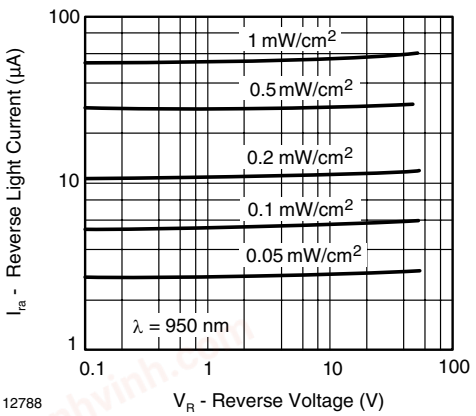


Fig. 4 - Reverse Light Current vs. Reverse Voltage

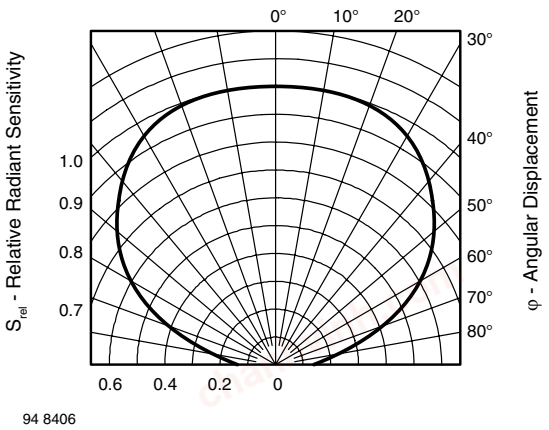


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

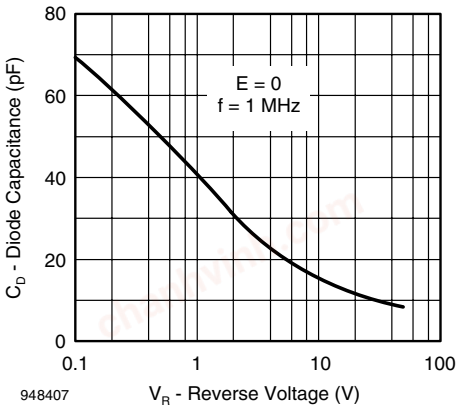


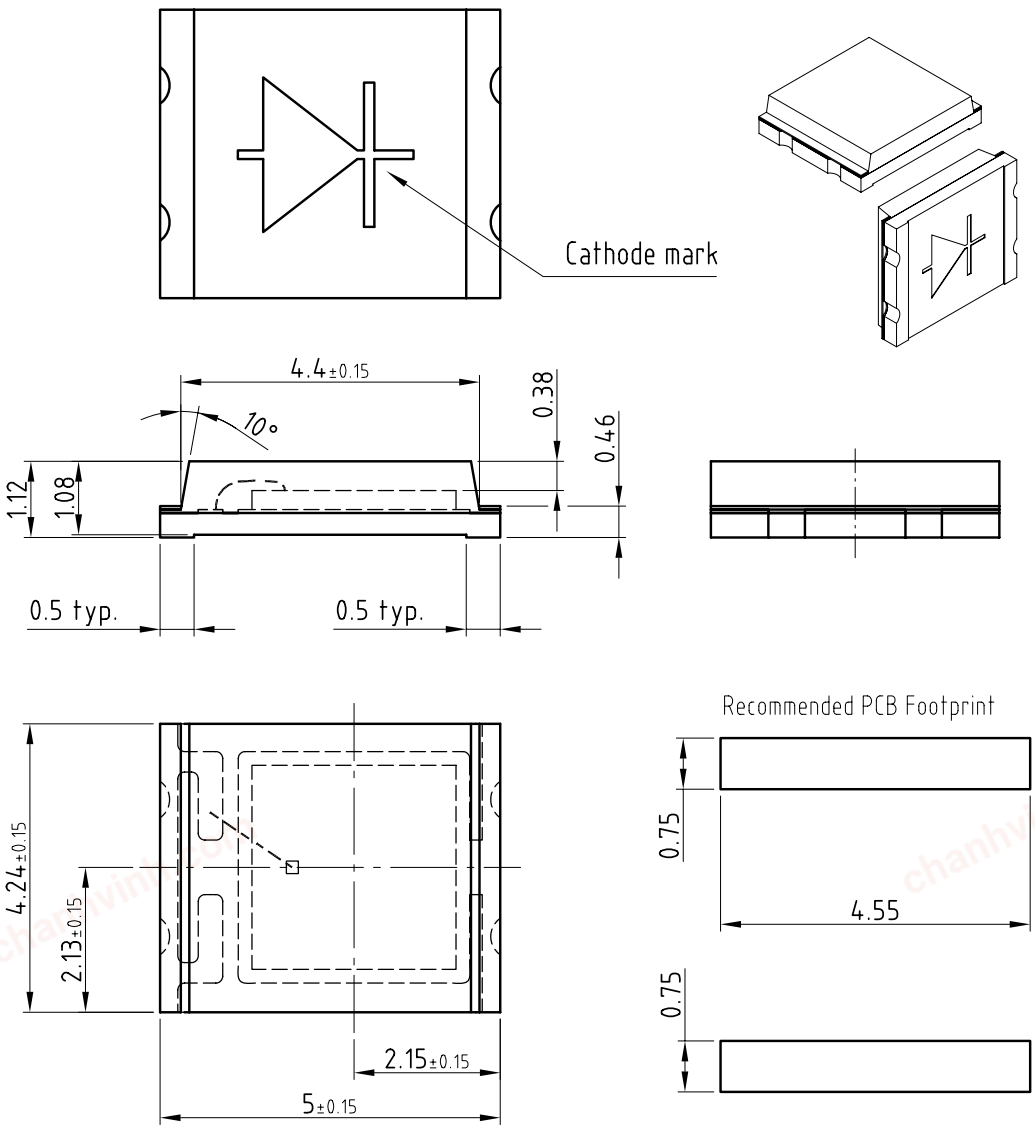
Fig. 5 - Diode Capacitance vs. Reverse Voltage

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TEMD5010X01

Vishay Semiconductors — Silicon PIN Photodiode

PACKAGE DIMENSIONS in millimeters



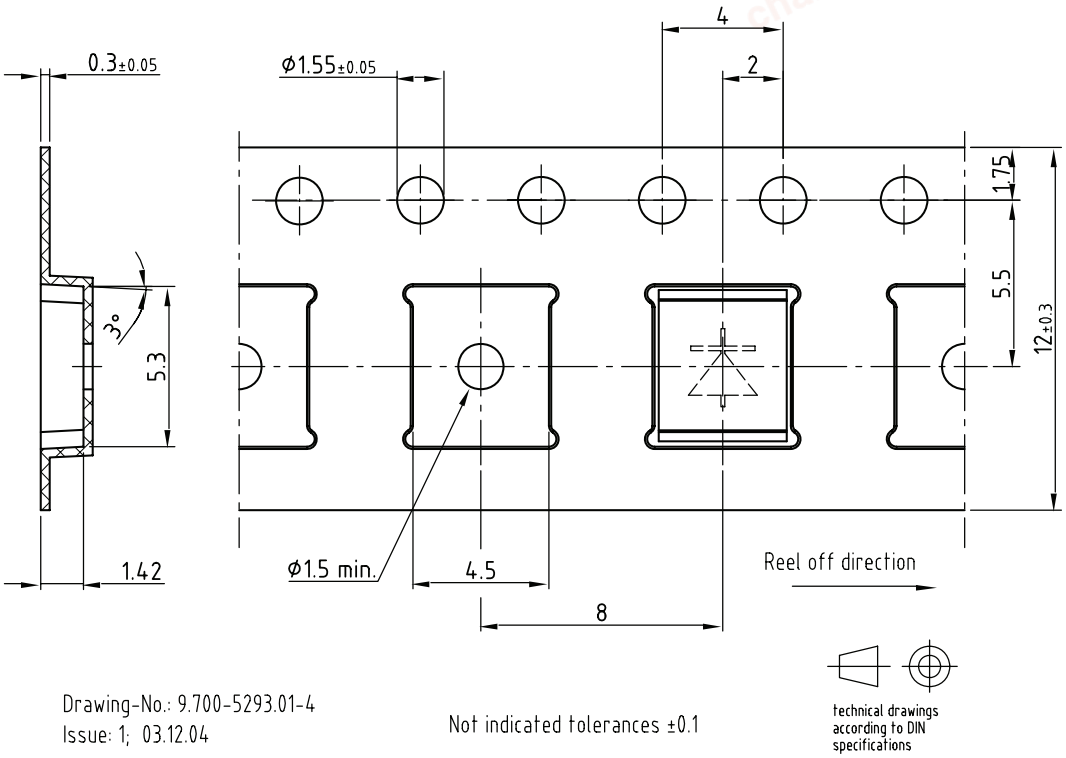
technical drawings according to DIN specifications

Drawing-No.: 6.541-5060.01-4
Issue: 3; 05.02.08
20536

Not indicated tolerances ± 0.1

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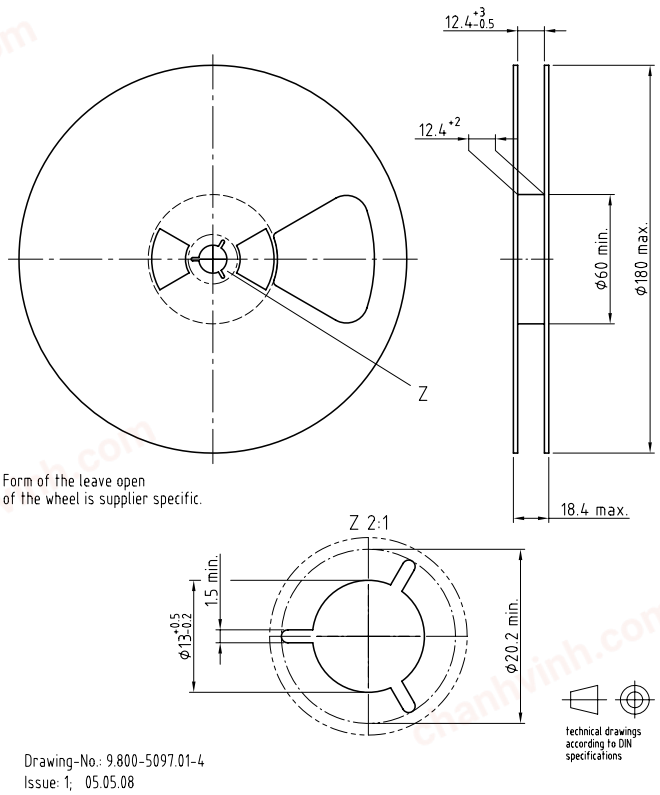
TAPING DIMENSIONS in millimeters



Drawing-No.: 9.700-5293.01-4
Issue: 1; 03.12.04
20537

Not indicated tolerances ±0.1

REEL DIMENSIONS in millimeters



Form of the leave open
of the wheel is supplier specific.

Drawing-No.: 9.800-5097.01-4
Issue: 1; 05.05.08
20874

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SOLDER PROFILE

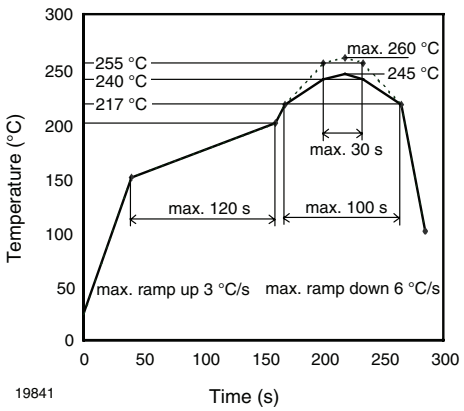


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020D

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:
Moisture sensitivity: level 4
Floor life: 72 h
Conditions: T_{amb} < 30 °C, RH < 60 %

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions:
192 h at 40 °C (+ 5 °C), RH < 5 %
or
96 h at 60 °C (+ 5 °C), RH < 5 %.

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Disclaimer

All product specifications and data are subject to change without notice.

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